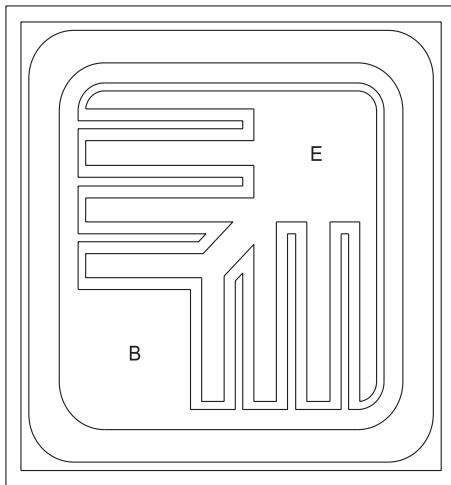


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	30 x 30 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	8.0 x 8.0 MILS
Emitter Bonding Pad Area	7.6 x 7.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

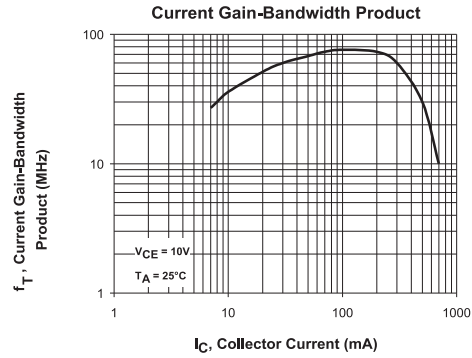
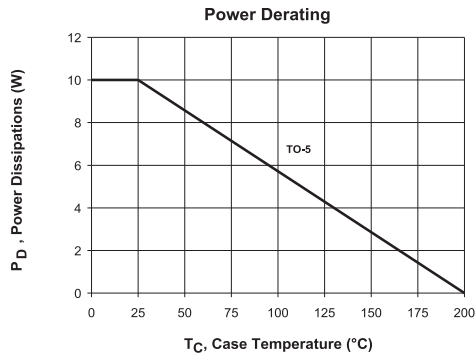
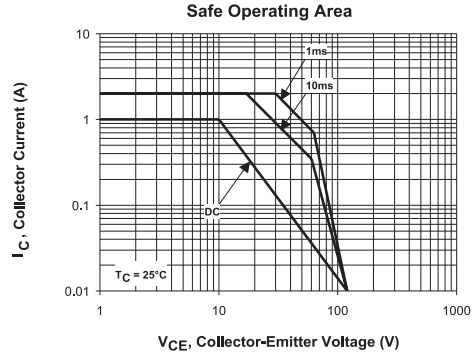
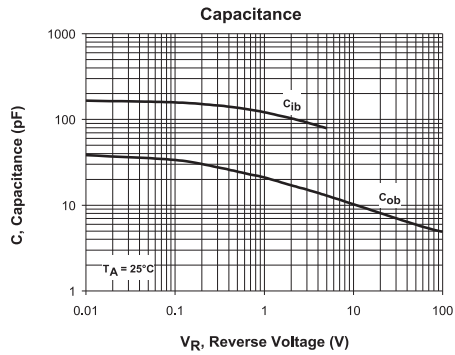
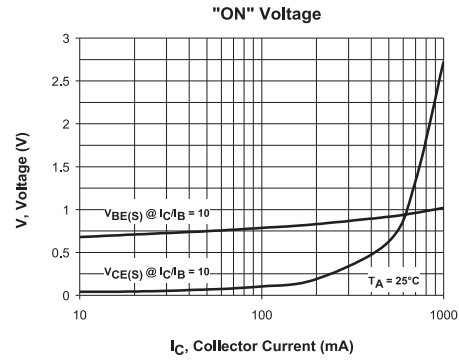
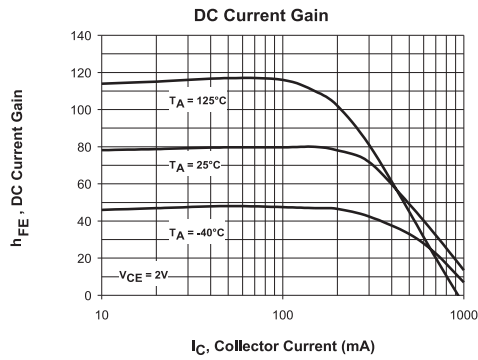
12,550

PRINCIPAL DEVICE TYPES

2N5680

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R2 (1-August 2002)



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